

Description

The SI2310-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$$\begin{split} V_{\text{DS}} &= 60 V \ \text{I}_{\text{D}} = 3 \text{A} \\ \text{R}_{\text{DS(ON)}} &< 89 \text{m} \Omega \ @ \text{V}_{\text{GS}} = 10 V \end{split}$$

Application

Battery protection Load switch Uninterruptible power supply

Package Marking and Ordering Information

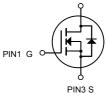
Product ID	Pack	Marking	Qty(PCS)
SI2310-HXY	SOT-23	S10	3000PCS

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit	
Vds	Drain-Source Voltage	60	V	
Vgs	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous	3	А	
Ы	Drain Current-Pulsed (Note 1)	10	A	
PD	Maximum Power Dissipation	1.7	W	
Tj,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	73.5	°C/W	







N-Channel MOSFET



Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)				•		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	0.8	1.3	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A	-	80	89	mΩ
Drain-Source On-State Resistance		V _{GS} =4.5V, I _D =1.5A	-	89	115	mΩ
Forward Transconductance	g fs	V _{DS} =15V,I _D =2A		3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	510	-	PF
Output Capacitance	Coss	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	34	-	PF
Reverse Transfer Capacitance	Crss		-	26	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t _{d(on)}		-	6	-	nS
Turn-on Rise Time	tr	V_{DD} =30V,I _D =1.5A	-	15	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =1 Ω	-	15	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	\/	-	7.5	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =30V,I _D =3A, V _{GS} =4.5V	-	1.4	-	nC
Gate-Drain Charge	Q _{gd}	v _{GS} -4.3v	-	3	-	nC
Drain-Source Diode Characteristics	·		•	•		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3	А

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

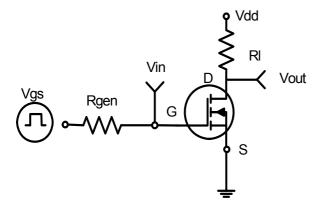


Figure 1:Switching Test Circuit

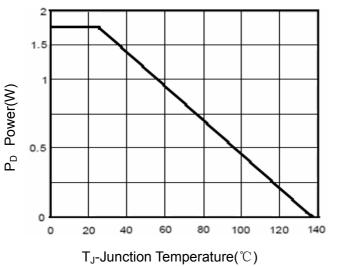
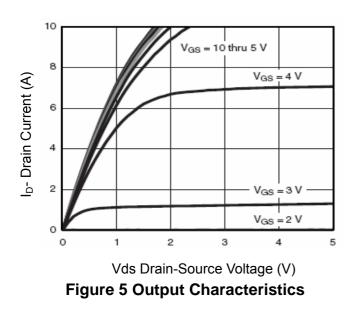


Figure 3 Power Dissipation



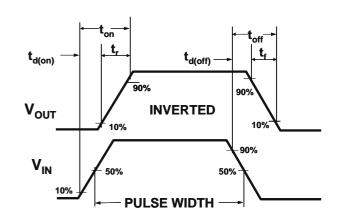
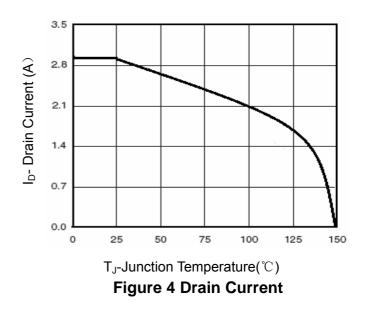
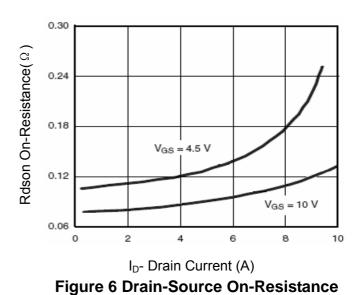
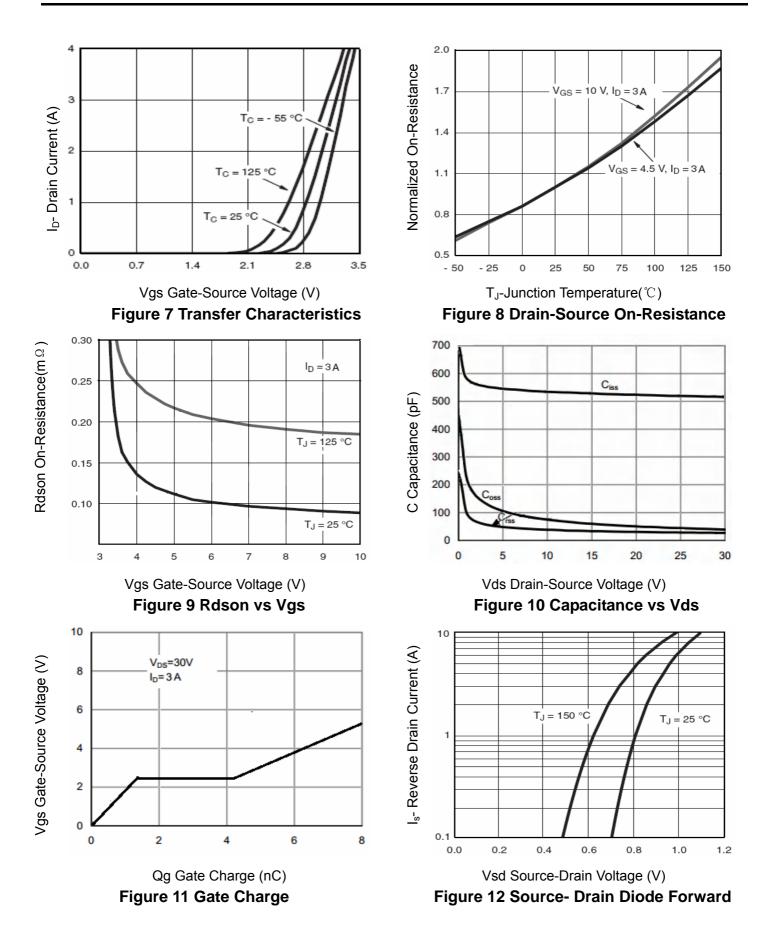


Figure 2:Switching Waveforms











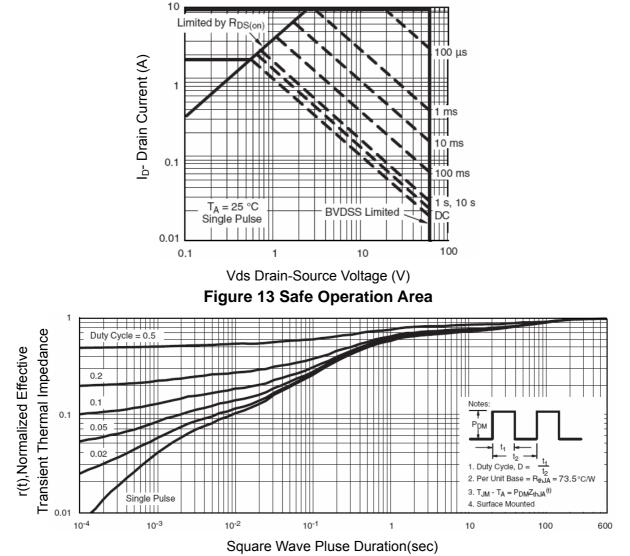
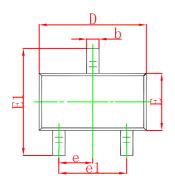
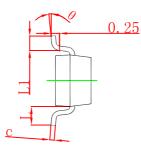


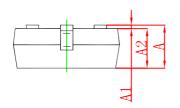
Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

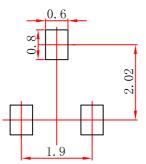






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
e	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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